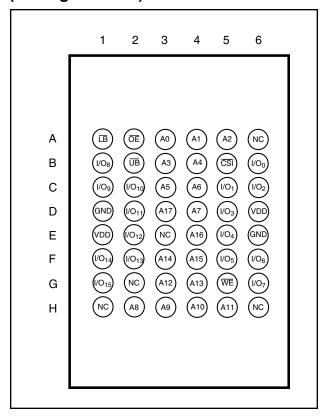


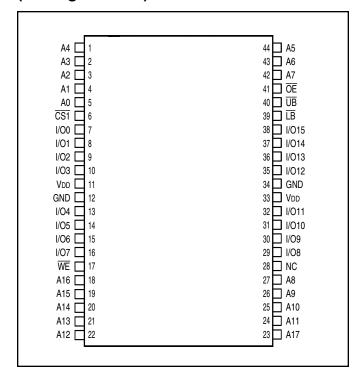
PIN CONFIGURATIONS 48- ball mini BGA (6mm x 8mm) (Package Code B)



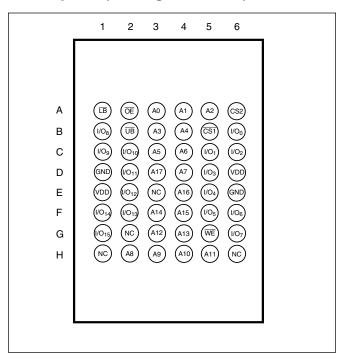
PIN DESCRIPTIONS

A0-A17	Address Inputs
I/O0-I/O15	Data Inputs/Outputs
CS1, CS2	Chip Enable Input
ŌĒ	Output Enable Input
WE	Write Enable Input
LB	Lower-byte Control (I/O0-I/O7)
ŪB	Upper-byte Control (I/O8-I/O15)
NC	No Connection
V _{DD}	Power
GND	Ground

44-Pin mini TSOP (Type II) (Package Code T)



48-Pin mini BGA (6mm x 8mm)* 2 CS Option (Package Code B2)



^{*}Available upon request



TRUTH TABLE

							I/O PIN			
Mode	WE	CS1	CS2	ŌĒ	LΒ	ŪB	1/00-1/07	I/O8-I/O15	VDD Current	
Not Selected	Х	Н	Х	Х	Х	Х	High-Z	High-Z	ISB1, ISB2	
	Χ	Χ	L	Χ	Χ	Χ	High-Z	High-Z	ISB1, ISB2	
	Χ	Χ	Χ	Χ	Н	Н	High-Z	High-Z	ISB1, ISB2	
Output Disabled	Н	L	Н	Н	L	Х	High-Z	High-Z	Icc	
	Н	L	Н	Н	X	L	High-Z	High-Z	Icc	
Read	Н	L	Н	L	L	Н	D ouт	High-Z	Icc	
	Н	L	Н	L	Н	L	High-Z	D out		
	Н	L	Н	L	L	L	D оит	D оит		
Write	L	L	Н	Х	L	Н	Din	High-Z	Icc	
	L	L	Н	Χ	Н	L	High-Z	DIN		
	L	L	Н	Χ	L	L	DIN	DIN		

ABSOLUTE MAXIMUM RATINGS(1)

Symbol	Parameter	Value	Unit
VTERM	Terminal Voltage with Respect to GND	-0.5 to V _{DD} + 0.5	V
VDD	VDD Relates to GND	-0.3 to 4.0	V
Тѕтс	Storage Temperature	-65 to +150	°C
Рт	Power Dissipation	1.0	W

Notes:

CAPACITANCE(1,2)

Symbol	Parameter	Conditions	Max.	Unit	
CIN	Input Capacitance	$V_{IN} = 0V$	6	pF	
C _{I/O}	Input/Output Capacitance	Vout = 0V	8	pF	

- 1. Tested initially and after any design or process changes that may affect these parameters.
- 2. Test conditions: $TA = 25^{\circ}C$, f = 1 MHz, VDD = 3.3V.

Stress greater than those listed under ABSOLUTE MAXIMUM RATINGS may cause permanent damage to the device. This is a stress rating only and functional operation of the device at these or any other conditions above those indicated in the operational sections of this specification is not implied. Exposure to absolute maximum rating conditions for extended periods may affect reliability.



ACTEST CONDITIONS

Parameter	Unit (2.3V-3.6V)	Unit (3.3V <u>+</u> 5%)	Unit (1.65V-2.2V)	
Input Pulse Level	0.4V to VDD - 0.3V	0.4V to V _{DD} - 0.3V	0.4V to V _{DD} - 0.3V	
Input Rise and Fall Times	1V/ ns	1V/ ns	1V/ ns	
Input and Output Timing and Reference Level (VRef)	VDD /2	<u>VDD</u> + 0.05 2	0.9V	
Output Load	See Figures 1 and 2	See Figures 1 and 2	See Figures 1 and 2	
R1 (Ω)	1005	1213	13500	
R2 (Ω)	820	1378	10800	
Vтм (V)	3.0V	3.3V	1.8V	

ACTEST LOADS

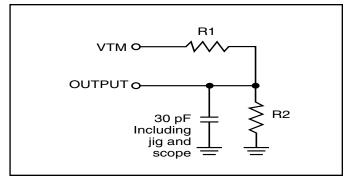


Figure 1.

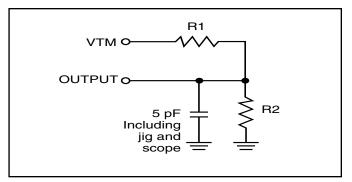


Figure 2.



DC ELECTRICAL CHARACTERISTICS (Over Operating Range)

 $V_{DD} = 3.3V \pm 5\%$

Symbol	Parameter Test Conditions		Min.	Max.	Unit
Vон	Output HIGH Voltage	$V_{DD} = Min., I_{OH} = -1 \text{ mA}$	2.4	_	V
Vol	Output LOW Voltage	$V_{DD} = Min., I_{OL} = 2.1 \text{ mA}$	_	0.4	V
VIH	Input HIGH Voltage		2	$V_{DD} + 0.3$	V
VIL	Input LOW Voltage(1)		-0.3	0.8	V
ILI	Input Leakage	$GND \leq V_{IN} \leq V_{DD}$	-1	1	μΑ
ILO	Output Leakage	GND ≤ Vouт ≤ VDD, Outputs Disabled	-1	1	μA

Note:

DC ELECTRICAL CHARACTERISTICS (Over Operating Range)

$V_{DD} = 2.3V - 3.6V$

Symbol	Parameter	Test Conditions	Min.	Max.	Unit
Vон	Output HIGH Voltage	$V_{DD} = Min., I_{OH} = -1.0 \text{ mA}$	1.8	_	V
Vol	Output LOW Voltage	$V_{DD} = Min., I_{OL} = 2.1 \text{ mA}$	_	0.4	V
VIH	Input HIGH Voltage		2.0	$V_{DD} + 0.3$	V
VIL	Input LOW Voltage(1)		-0.3	0.8	V
Iц	Input Leakage	$GND \leq Vin \leq Vdd$	-1	1	μΑ
ILO	Output Leakage	$GND \leq V_{OUT} \leq V_{DD}$, Outputs Disabled	-1	1	μΑ

Note

DC ELECTRICAL CHARACTERISTICS (Over Operating Range)

$V_{DD} = 1.65V-2.2V$

Symbol	Parameter	Test Conditions	V DD	Min.	Max.	Unit
Vон	Output HIGH Voltage	Ioh = -0.1 mA	1.65-2.2V	1.4	_	V
Vol	Output LOW Voltage	IoL = 0.1 mA	1.65-2.2V	_	0.2	V
VIH	Input HIGH Voltage		1.65-2.2V	1.4	V _{DD} + 0.2	V
VIL ⁽¹⁾	Input LOW Voltage		1.65-2.2V	-0.2	0.4	V
lu	Input Leakage	$GND \leq Vin \leq Vdd$		-1	1	μA
ILO	Output Leakage	$GND \leq Vout \leq Vdd$, (Outputs Disabled	-1	1	μΑ

^{1.} V_{IL} (min.) = -0.3V DC; V_{IL} (min.) = -2.0V AC (pulse width < 10 ns). Not 100% tested. V_{IH} (max.) = V_{DD} + 0.3V DC; V_{IH} (max.) = V_{DD} + 2.0V AC (pulse width < 10 ns). Not 100% tested.

^{1.} V_{IL} (min.) = −0.3V DC; V_{IL} (min.) = −2.0V AC (pulse width < 10 ns). Not 100% tested. V_{IH} (max.) = V_{DD} + 0.3V DC; V_{IH} (max.) = V_{DD} + 2.0V AC (pulse width < 10 ns). Not 100% tested.

^{1.} V_{IL} (min.) = −0.3V DC; V_{IL} (min.) = −2.0V AC (pulse width < 10 ns). Not 100% tested. V_{IH} (max.) = V_{DD} + 0.3V DC; V_{IH} (max.) = V_{DD} + 2.0V AC (pulse width < 10 ns). Not 100% tested.

IS62WV25616DALL/DBLL, IS65WV25616DBLL



OPERATING RANGE (VDD)

Range	Ambient Temperature	V DD	Speed	
Commercial	0°C to +70°C	1.65V-2.2V	45ns	
Industrial	–40°C to +85°C	1.65V-2.2V	55ns	
Automotive	-40°C to +125°C	1.65V-2.2V	55ns	

OPERATING RANGE (VDD)

<u> </u>	17 11 TOIL (T D D)			
Range	Ambient Temperature	V _{DD} (45 ns)	Vdd (35 ns)	
Commercial	0°C to +70°C	2.3V-3.6V	3.3V <u>+</u> 5%	
Industrial	–40°C to +85°C	2.3V-3.6V	3.3V <u>+</u> 5%	
Automotive (A1)	-40°C to +85°C	2.3V-3.6V	3.3V+5%	

OPERATING RANGE (VDD)

Range	Ambient Temperature	Vdd (45 ns)
Automotive (A3) -40°C to +125°C	2.3V-3.6V

POWER SUPPLY CHARACTERISTICS⁽¹⁾ (Over Operating Range)

				-3	35	-4	15	-5	55	
Symbol	Parameter	Test Conditions		Min.	Max.	Min.	Max.	Min.	Max.	Unit
Icc	VDD Dynamic Operating	V _{DD} = Max.,	Com.	_	20	_	15	_	15	mA
	Supply Current	IOUT = 0 mA, f = fMAX	Ind./Auto A1	_	25	_	18	_	15	
		CE = VIL	Auto. A3	_	30	_	25	_	25	
		$V_{IN} \ge V_{DD} - 0.3V$, or	typ. ⁽²⁾	1	0					
		$V_{IN} \leq 0.4V$								
lcc1	Operating	$V_{DD} = Max.,$	Com.	_	3	_	3	_	3	mA
	Supply Current	IOUT = 0 mA, f = 0	Ind./Auto A1	_	3	_	3	_	3	
		$\overline{CE} = V_{IL}$	Auto. A3	_	3	_	3	_	3	
		$V_{IN} \ge V_{DD} - 0.3V$, or								
		$V_{IN} \leq 0.4V$								
IsB2	CMOS Standby	V _{DD} = Max.,	Com.	_	5	_	5	_	5	μA
	Current (CMOS Inputs)	$\overline{\text{CS1}} \ge \text{V}_{\text{DD}} - 0.2\text{V},$	Ind./Auto A1	_	10	_	10	_	10	
		$CS2 \leq 0.2V$,	Auto. A3	_	30	_	30	_	30	
		$V_{\text{IN}} \ge V_{\text{DD}} - 0.2V$, or	typ. ⁽²⁾	2	2					
		$Vin \leq 0.2V$, $f = 0$								
	OR									
	ULB Control	$V_{DD} = Max., \overline{CS1} = V_{IN} \le 0.2V, f = 0; \overline{UB}$,							
		V IIV ≥ U.∠ V, I − U, UD	/ LD = VDD = 0.	∠ v						

- 1. At $f = f_{MAX}$, address and data inputs are cycling at the maximum frequency, f = 0 means no input lines change.
- 2. Typical values are measured at $V_{DD} = 3.0V$, $T_A = 25^{\circ}C$ and not 100% tested.





READ CYCLE SWITCHING CHARACTERISTICS⁽¹⁾ (Over Operating Range)

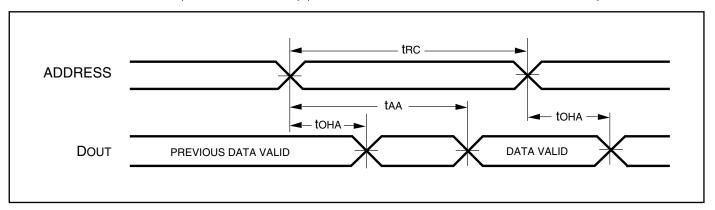
		35	ns	45	i ns	55	ns	
Symbol	Parameter	Min.	Max.	Min.	Max.	Min.	Max.	Unit
t rc	Read Cycle Time	35		45	_	55	_	ns
taa	Address Access Time	_	35	_	45	_	55	ns
t oha	Output Hold Time	10	_	10	_	10	_	ns
tacs1/tacs2	CS1/CS2 Access Time	_	35	_	45	_	55	ns
tdoe	OE Access Time	_	10	_	20	_	25	ns
thzoe ⁽²⁾	OE to High-Z Output	0	10	0	15	0	20	ns
tLZOE ⁽²⁾	OE to Low-Z Output	3	_	5	_	5	_	ns
thzcs1/thzcs2(2)	CS1/CS2 to High-Z Output	0	10	0	15	0	20	ns
tLZCS1/tLZCS2 ⁽²⁾	CS1/CS2 to Low-Z Output	5	_	5	_	10	_	ns
t BA	LB, UB Access Time	_	35	_	45	_	55	ns
tнzв	LB, UB to High-Z Output	0	15	0	15	0	20	ns
t LZB	LB, UB to Low-Z Output	0	_	0	_	0	_	ns

^{1.} Test conditions assume signal transition times of 5 ns or less, timing reference levels of 0.9V/1.5V, input pulse levels of 0.4 to VDD-0.2V/VDD-0.3V and output loading specified in Figure 1.

^{2.} Tested with the load in Figure 2. Transition is measured ±500 mV from steady-state voltage. Not 100% tested.

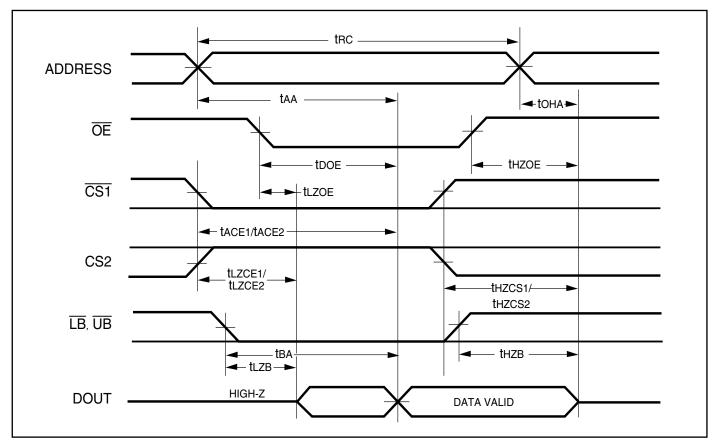


READ CYCLE NO. 1^(1,2) (Address Controlled) ($\overline{CS1} = \overline{OE} = V_{IL}$, $\overline{CS2} = \overline{WE} = V_{IH}$, \overline{UB} or $\overline{LB} = V_{IL}$)



AC WAVEFORMS

READ CYCLE NO. 2^(1,3) ($\overline{CS1}$, CS2, \overline{OE} , AND $\overline{UB}/\overline{LB}$ Controlled)



- WE is HIGH for a Read Cycle.
 The device is continuously selected. OE, CS1, UB, or LB = VIL. CS2=WE=VIH.
- 3. Address is valid prior to or coincident with $\overline{\text{CS1}}$ LOW transition.





WRITE CYCLE SWITCHING CHARACTERISTICS(1,2) (Over Operating Range)

		35	ns	45	ns	55	ns	
Symbol	Parameter	Min.	Max.	Min.	Max.	Min.	Max.	Unit
twc	Write Cycle Time	35	_	45	_	55	_	ns
tscs1/tscs2	CS1/CS2 to Write End	25	_	35	_	45	_	ns
taw	Address Setup Time to Write End	25	_	35	_	45	_	ns
t ha	Address Hold from Write End	0	_	0	_	0	_	ns
t sa	Address Setup Time	0	_	0	_	0	_	ns
t PWB	LB, UB Valid to End of Write	25	_	35	_	45	_	ns
t PWE	WE Pulse Width	25	_	35	_	40	_	ns
tsD	Data Setup to Write End	20	_	20	_	25	_	ns
t HD	Data Hold from Write End	0	_	0	_	0	_	ns
thzwe ⁽³⁾	WE LOW to High-Z Output	_	10	_	20	_	20	ns
tLZWE ⁽³⁾	WE HIGH to Low-Z Output	3	_	5	_	5	_	ns

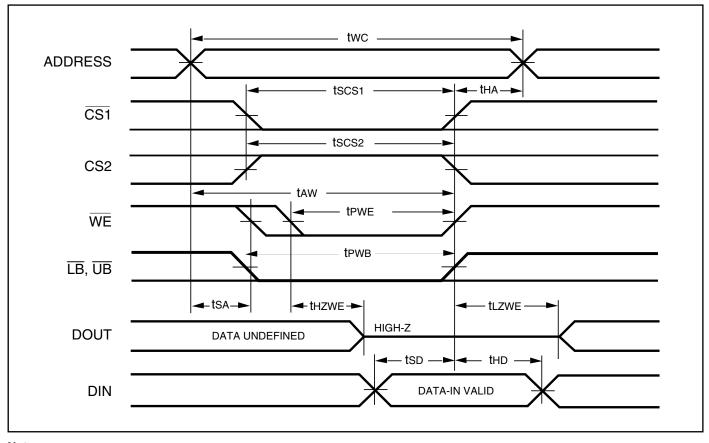
^{1.} Test conditions assume signal transition times of 5 ns or less, timing reference levels of 0.9V/1.5V, input pulse levels of 0.4V to VDD-0.2V/VDD-0.3V and output loading specified in Figure 1.

^{2.} The internal write time is defined by the overlap of CS1 LOW, CS2 HIGH and UB or LB, and WE LOW. All signals must be in valid states to initiate a Write, but any one can go inactive to terminate the Write. The Data Input Setup and Hold timing are referenced to the rising or falling edge of the signal that terminates the write.

^{3.} Tested with the load in Figure 2. Transition is measured ±500 mV from steady-state voltage. Not 100% tested.



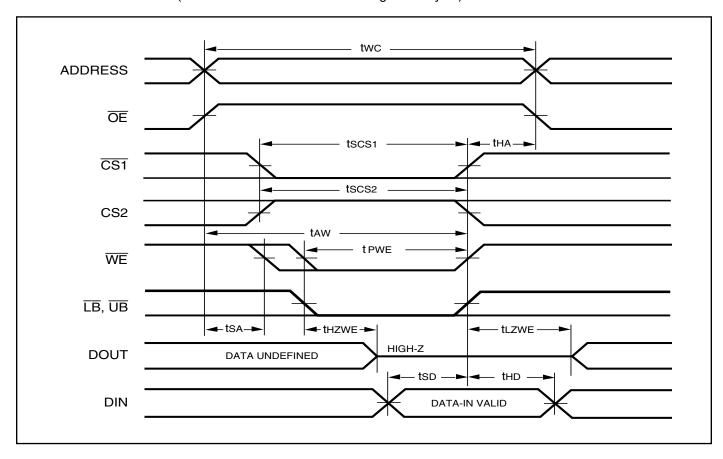
WRITE CYCLE NO. $1^{(1,2)}$ ($\overline{CS1}$ Controlled, \overline{OE} = HIGH or LOW)



- 1. WRITE is an internally generated signal asserted during an overlap of the LOW states on the $\overline{\text{CS1}}$, CS2 and $\overline{\text{WE}}$ inputs and at least one of the $\overline{\text{LB}}$ and $\overline{\text{UB}}$ inputs being in the LOW state.
- 2. WRITE = $(\overline{CS1})$ [(\overline{LB}) = (\overline{UB})] (\overline{WE}) .

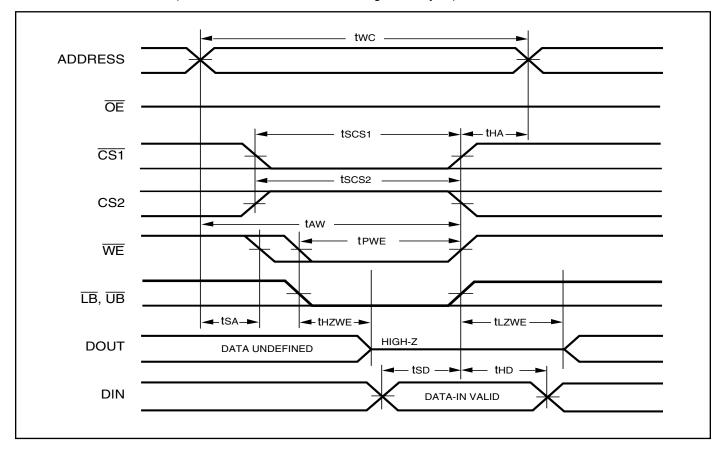


WRITE CYCLE NO. 2 (WE Controlled: OE is HIGH During Write Cycle)



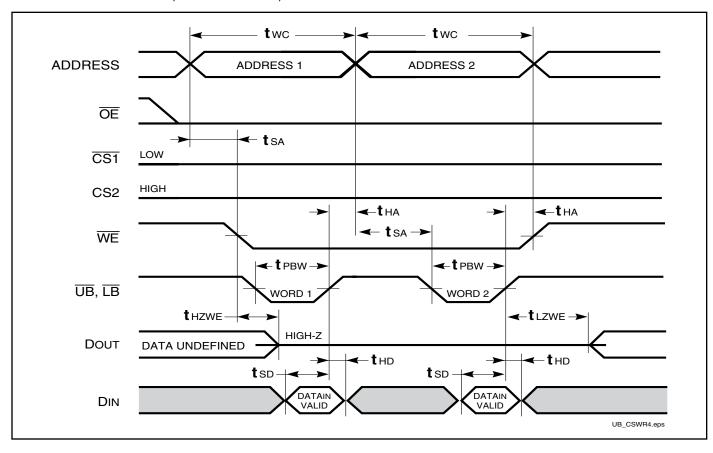


WRITE CYCLE NO. 3 (WE Controlled: OE is LOW During Write Cycle)





WRITE CYCLE NO. 4 (UB/LB Controlled)



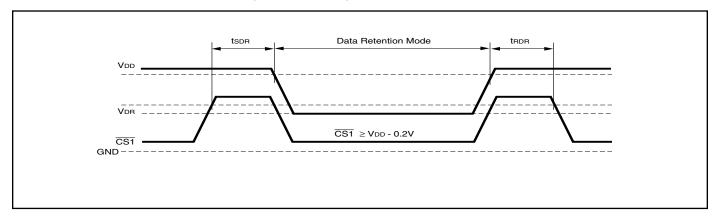


DATA RETENTION SWITCHING CHARACTERISTICS

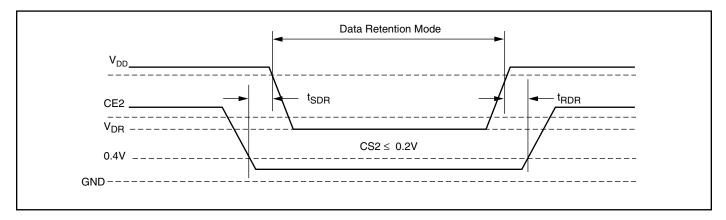
Symbol	Parameter	Test Condition		Min.		Max.	Unit
V _{DR}	VDD for Data Retention	See Data Retention Waveform		1.2		3.6	V
ldr	Data Retention Current	$V_{DD} = 1.2V, \overline{CS1} \ge V_{DD} - 0.2V$	Com. Ind. Auto. typ. ⁽¹⁾		1	3 7 20	μА
tsdr	Data Retention Setup Time	See Data Retention Waveform		0	_	ns	
trdr	Recovery Time	See Data Retention Waveform		trc	_	ns	

Note: 1. Typical values are measured at $V_{DD} = 3.0V$, $T_A = 25^{\circ}C$ and not 100% tested.

DATA RETENTION WAVEFORM (CS1 Controlled)



DATA RETENTION WAVEFORM (CS2 Controlled)





ORDERING INFORMATION

IS62WV25616DALL (1.65V-2.2V)

Commercial Range: 0°C to +70°C

Speed (ns)	Order Part No.	Package
70	IS62WV25616DALL-55TL	TSOP, Lead-free

Industrial Range: -40°C to +85°C

Speed (ns)	Order Part No.	Package
55	IS62WV25616DALL-55TI	TSOP
	IS62WV25616DALL-55TLI	TSOP, Lead-free
55	IS62WV25616DALL-55BI	mini BGA (6mmx8mm)
	IS62WV25616DALL-55BLI	mini BGA (6mmx8mm), Lead-free

IS62WV25616DBLL (2.3V - 3.6V)

Industrial Range: -40°C to +85°C

Speed (ns)	Order Part No.	Package
45	IS62WV25616DBLL-45TI	TSOP
	IS62WV25616DBLL-45TLI	TSOP, Lead-free
45	IS62WV25616DBLL-45BI	mini BGA (6mmx8mm)
	IS62WV25616DBLL-45BLI	mini BGA (6mmx8mm), Lead-free
55	IS62WV25616DBLL-55TLI	TSOP, Lead-free

IS65WV25616DBLL (2.3V - 3.6V)

Automotive (A1) Range: -40°C to +85°C

Speed (ns)	Order Part No.	Package
45	IS65WV25616DBLL-45CTLA1	TSOP, Lead-free, Copper Leadframe

Automotive (A3) Range: -40°C to +125°C

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Speed (ns)	Order Part No.	Package
55	IS65WV25616DBLL-55CTLA3	TSOP, Lead-free, Copper Leadframe



